

***Remarks***

Reconsideration of this Application is respectfully requested.

Claims 18-20 are pending in the application, with claim 18 being the independent claims.

Claims 11-17 are cancelled by this amendment without any disclaimer or a prejudice to.

Based on the amendments and following remarks, Applicants respectfully request that the Examiner reconsider all outstanding objections and rejections and they be withdrawn.

***Rejection under 35 U.S.C. § 102***

In the Office Action mailed on September 14, 2001, the Examiner rejected claim 10 under 35 U.S.C. § 102 as being anticipated by various prior art references, such as U.S. Patent Nos. 5,259,881; 5,512,320; and 6,013,162 respectively issued to Edwards *et al.* ("Edwards"); Turner *et al.* ("Turner"); and Kobayashi *et al.* ("Kobayashi").

Claim 10 has been cancelled by this amendment and new claims 18-20 have been added. Therefore, the Examiner's rejection over claim 10 has become moot. New claims 18-20 recite an apparatus for depositing a layer on a substrate, comprising: a chemical vapor deposition chamber that deposits thin layers by a chemical vapor deposition method; and a process chamber that deposits a metal layer on the substrate by a sputtering method.

Nowhere in the cited reference, discloses such features. Therefore, it is respectfully submitted that new claims 18-20 are patentable over the cited references.

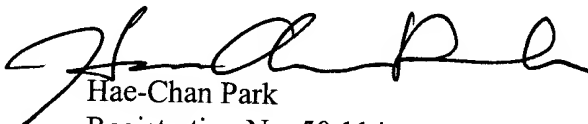
As such, it is respectfully requested that all the outstanding rejections and objections be withdrawn and new claims 18-20 be allowed.

***Conclusion***

All of the stated grounds of objection and rejection have been properly traversed, accommodated, or rendered moot. Applicants therefore respectfully request that the Examiner reconsider all presently outstanding objections and rejections and that they be withdrawn. Applicants believe that a full and complete response has been made to the outstanding Office Action and, as such, the present application with claims 1-8 and 10-11 is in condition for allowance. If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at the number provided.

Prompt and favorable consideration of this Amendment is respectfully requested.

Respectfully submitted,

  
Hae-Chan Park  
Registration No. 50,114

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**McGUIRE WOODS, LLP**  
1750 Tysons Boulevard  
Suite 1800  
McLean, VA 22102-4215  
(703) 712-5365 (Direct Phone)  
(703) 712-5280 (Direct Fax)

**Versions with Markings to Show Changes Made**

***In the Claims:***

Please cancel claims 11-17 without any disclaimer or a prejudice to and add new claim 18 as follows:

18. (New) An apparatus for depositing a layer on a substrate, comprising:  
a load lock chamber that receives a substrate;  
a preheat chamber that heats the substrate before deposition;  
a chemical vapor deposition chamber that deposits thin layers by a chemical vapor deposition method; and  
a process chamber that deposits a metal layer on the substrate by a sputtering method,  
wherein the substrate is transferred among the chambers in a vacuum while not exposed to ambient atmosphere.

19. (New) The apparatus of claim 18, wherein the substrate is first placed in the load lock chamber and moved into the preheat chamber for preheating.

20. (New) The apparatus of claim 19, wherein the substrate is then moved to the chemical vapor deposition chamber for deposition of silicon.

21. (New) The apparatus of claim 20, wherein the substrate is then moved to the process chamber to deposit metal layer on the substrate by sputtering.